



Substitute for form 1449A/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Application Number	09/640,519
		Filing Date	August 17, 2000
		First Named Inventor	Hiroaki NAKAOKA
		Art Unit	2818
		Examiner Name	David Vu
Sheet 1 of 1	Attorney Docket Number	740819-408	

U.S. PATENT DOCUMENTS					
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
		US-			
		US-			
		US-			

FOREIGN PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code ³	Number ⁴ Kind Code ⁵ (if known)			

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
DV		LAI, ET AL., "A COMPARISON BETWEEN NO-ANNEALED 0 ₂ -AND N ₂ O-GROWN GATE DIELECTRICS", PROCEEDINGS 1998 IEEE HONG KONG ELECTRON DEVICES MEETING, PP. 36-39, AUGUST 29, 1998, CHINA	
DV		LIN, ET AL., "LEAKAGE CURRENT, RELIABILITY CHARACTERISTICS, AND BORON PENETRATION OF ULTRA-THIN (32-36Å) O ₂ -OXIDES AND N ₂ O/NO OXYNITRIDES", IEDM 96, PP. 331-334, 1996	
DV		SUN, ET AL., "MOS CHARACTERISTICS OF N ₂ O-GROWN AND NO-ANNEALED OXYNITRIDES", 4 TH INTERNATIONAL TECHNOLOGY PROCEEDINGS, PP. 90-92, NOVEMBER 1995	
DV		NOTICE OF REASONS OF REJECTION DATED DECEMBER 24, 2003	

Examiner Signature	<i>Phuland</i>	Date Considered	11/21/04
--------------------	----------------	-----------------	----------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.